

# -100V, SOT23/TDFN, Simple Swapper Hot-Swap Controllers

## ABSOLUTE MAXIMUM RATINGS

Terminal Voltage (with respect to GND, unless otherwise noted)  
 V<sub>EE</sub>, DRAIN, PGOOD, PGOOD ..... -120V to +0.3V  
 ON/OFF to V<sub>EE</sub> ..... -0.3V to +4V  
 GATE to V<sub>EE</sub> ..... -0.3V to +12V  
 Current into Any Pin ..... ±3mA

Continuous Power Dissipation (T<sub>A</sub> = +70°C)

6-Pin SOT23 (derate 9.1mW/°C above +70°C) ..... 727mW

6-Pin TDFN (derate 18.2mW/°C above +70°C) ..... 1454mW

Junction to Case Thermal Resistance,  $\theta_{JC}$  (TDFN) ..... 8.5°C/W

Maximum Junction Temperature ..... +150°C

Storage Temperature Range ..... -60°C to +150°C

Lead Temperature (soldering, 10s) ..... +300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ELECTRICAL CHARACTERISTICS

(V<sub>EE</sub> = -9V to -100V, GND = 0V, ON/OFF open circuit, T<sub>A</sub> = -40°C to +85°C, unless otherwise noted. Typical values are at V<sub>EE</sub> = -48V and T<sub>A</sub> = +25°C.) (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Supply Voltage	V <sub>EE</sub>			-100		-9	V
Supply Current	I <sub>GND</sub>	Measured at GND			0.5	1.3	mA
External Gate Drive	V <sub>GS</sub>	V <sub>GATE</sub> - V <sub>EE</sub>	V <sub>EE</sub> = -36V to -72V	7.5	9.5	11.6	V
			V <sub>EE</sub> = -100V	8	10	11.6	
			V <sub>EE</sub> = -9V	6	7		
Load Voltage Slew-Rate Magnitude	SR	I <sub>d</sub> V <sub>DRAIN</sub> /dt I, C <sub>LOAD</sub> = 10μF, V <sub>EE</sub> = -9V to -36V		4.5	10	17	V/ms
Default UVLO	V <sub>UVLO</sub>	V <sub>EE</sub>   increasing		-34.5	-31.5	-28.5	V
UVLO Hysteresis					3.5		V
ON/OFF Input Resistance	R <sub>ON/OFF</sub>			20	32	50	kΩ
Drain to V <sub>EE</sub> Resistance	R <sub>DV<sub>EE</sub></sub>				466		kΩ
ON/OFF Reference Threshold	V <sub>ON/OFF</sub>	(V <sub>ON/OFF</sub> - V <sub>EE</sub> ) increasing		1.14	1.26	1.38	V
ON/OFF Hysteresis					140		mV
Start Delay (Note 3)	t <sub>ON</sub>			150	300	500	ms
ON/OFF Off Delay (Note 4)	t <sub>OFF</sub>	V <sub>GATE</sub> - V <sub>EE</sub> < 1V		9	20	32	ms
Circuit-Breaker Threshold	V <sub>CB</sub>	V <sub>DRAIN</sub> - V <sub>EE</sub>	MAX590__AEUT	170	200	240	mV
			MAX590__BEUT	265	300	345	
			MAX590__CEUT	365	400	455	
Circuit-Breaker Delay (Note 5)	t <sub>CB</sub>	(V <sub>DRAIN</sub> - V <sub>EE</sub> ) > V <sub>CB</sub> until (V <sub>GATE</sub> - V <sub>EE</sub> ) < 1V, 200mV overdrive step	C <sub>GATE</sub> = 1nF		1.5	3	μs
			C <sub>GATE</sub> = 4.7nF		2.5	4.5	
			C <sub>GATE</sub> = 10nF		4	6	
Restart Delay (Note 3)	t <sub>RS</sub>	After circuit-breaker event, MAX590_A_EUT only		150	300	500	ms

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MAX5900/MAX5901

## ELECTRICAL CHARACTERISTICS (continued)

( $V_{EE} = -9V$  to  $-100V$ ,  $GND = 0V$ ,  $ON/OFF$  open circuit,  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , unless otherwise noted. Typical values are at  $V_{EE} = -48V$  and  $T_A = +25^{\circ}C$ .) (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
$\overline{PGOOD}$ (PGOOD) Assertion Threshold (Note 6)	$V_{PG}$	$V_{DRAIN} - V_{EE}$ ; MAX590_A, MAX590_L only		$0.75 \times V_{CB}$		mV
$\overline{PGOOD}$ (PGOOD) Output Low Voltage	$V_{OL}$	MAX5900, $V_{\overline{PGOOD}} - V_{EE}$ , $I_{OL} = 1mA$ ; MAX5901, $V_{PGOOD} - V_{EE}$ , $I_{OL} = 1mA$		0.6	1.65	V
Power-Good Output Open-Drain Leakage Current	$I_{OH}$	$V_{\overline{PGOOD}} - V_{EE} = 100V$ (MAX5900); $V_{PGOOD} - V_{EE} = 100V$ (MAX5901)		0.2	10	$\mu A$
Thermal Shutdown Temperature	$T_{SD}$	Junction temperature		+125		$^{\circ}C$
Thermal Shutdown Hysteresis	$T_{HY}$			15		$^{\circ}C$

**Note 1:** All currents into device pins are positive, all currents out of device pins are negative, and all voltages are referenced to GND, unless otherwise noted.

**Note 2:** All specifications are 100% tested at  $T_A = +25^{\circ}C$ . Specifications over  $-40^{\circ}C$  to  $+85^{\circ}C$  are guaranteed by characterization.

**Note 3:** This is the delay time from a valid on condition until  $V_{GS}$  begins rising. Valid on conditions are: the device is not in undervoltage lockout;  $ON/OFF$  is not driven low; and the device is not in thermal shutdown.

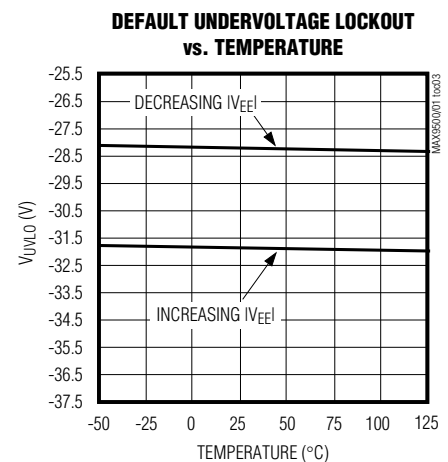
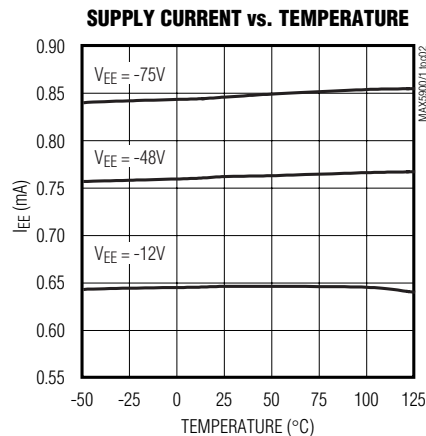
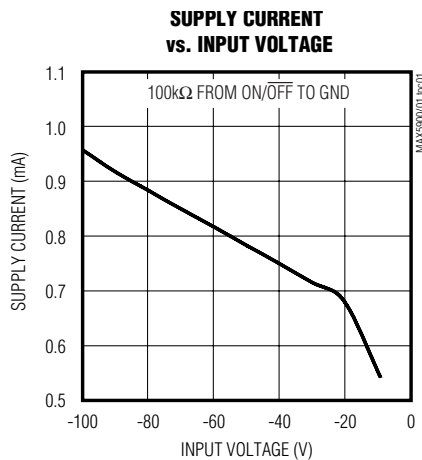
**Note 4:** This is the delay from a valid low on  $ON/OFF$  until  $V_{GS}$  falls. Pulses on  $ON/OFF$  less than  $t_{OFF}$  are ignored, offering glitch immunity.

**Note 5:** Guaranteed by design, not production tested.

**Note 6:** For a detailed description, see the *Power-Good Output* section.

## Typical Operating Characteristics

( $V_{EE} = -48V$ ,  $GND = 0V$ , and  $T_A = +25^{\circ}C$ , unless otherwise noted. See Figure 6 for test circuits.)

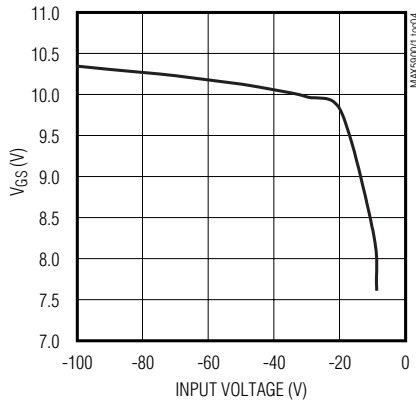


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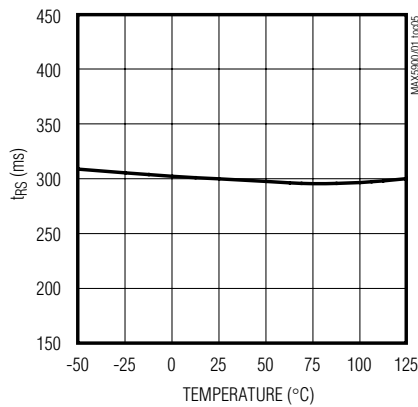
## Typical Operating Characteristics (continued)

( $V_{EE} = -48V$ ,  $GND = 0V$ , and  $T_A = +25^\circ C$ , unless otherwise noted. See Figure 6 for test circuits.)

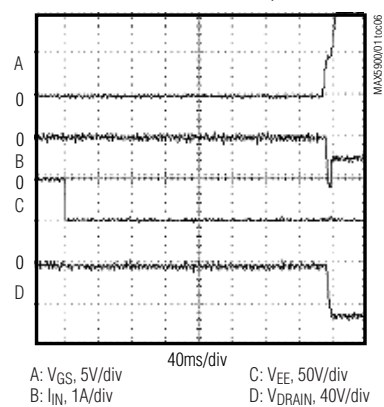
**GATE DRIVE VOLTAGE  
vs. INPUT VOLTAGE**



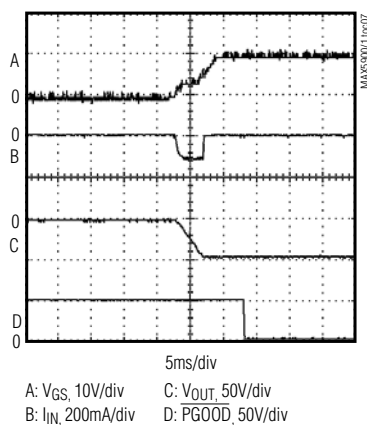
**RESTART DELAY  
vs. TEMPERATURE**



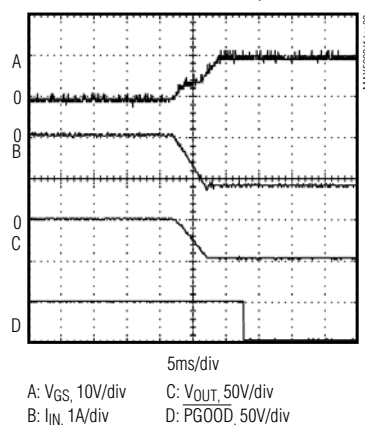
**STARTUP WAVEFORMS  
( $R_L = 90\Omega$ ,  $C_L = 100\mu F$ )**



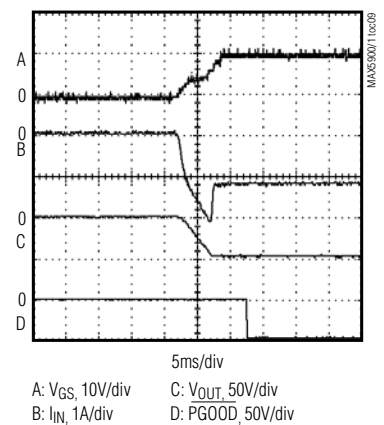
**STARTUP WAVEFORMS  
( $R_L = OPEN$ ,  $C_L = 10\mu F$ )**



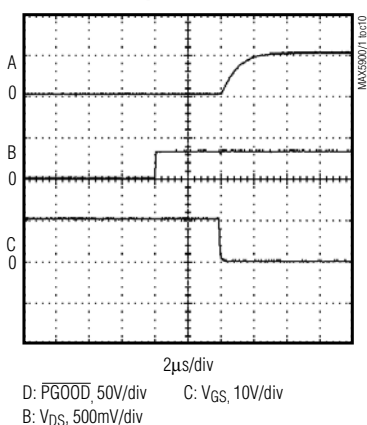
**STARTUP WAVEFORMS  
( $R_L = 40\Omega$ ,  $C_L = 10\mu F$ )**



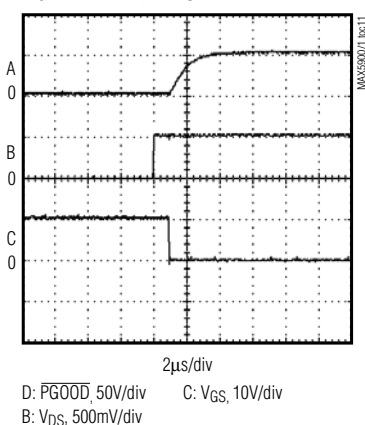
**STARTUP WAVEFORMS  
( $R_L = 40\Omega$ ,  $C_L = 100\mu F$ )**



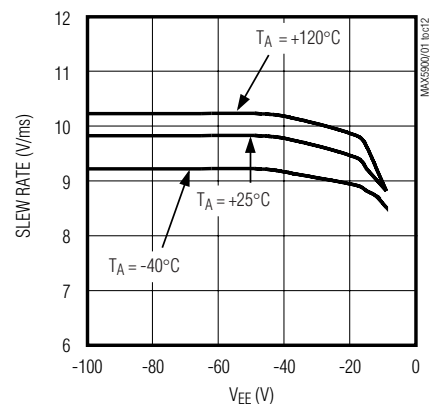
**CIRCUIT-BREAKER EVENT  
( $C_{GATE} = 1000pF$ ,  $V_{OVERDRIVE} = 20mV$ )**



**CIRCUIT-BREAKER EVENT  
( $C_{GATE} = 1000pF$ ,  $V_{OVERDRIVE} = 200mV$ )**



**SLEW RATE vs.  $V_{EE}$**



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## Pin Description

PIN		NAME	FUNCTION
MAX5900	MAX5901		
1	1	V <sub>EE</sub>	Negative Supply Voltage Input and External n-Channel MOSFET Source Connection
2	2	DRAIN	Drain Sense Input for External n-Channel MOSFET. Connect DRAIN as close as possible to the MOSFET's drain and use wide circuit traces to assure good thermal coupling between the MAX5900/MAX5901 and the MOSFET (see the <i>Layout Guidelines</i> section).
3	3	GATE	Gate Drive Output for External n-Channel MOSFET
4	4	GND	Ground Connection.
5	—	$\overline{\text{PGOOD}}$	Power-Good Output. $\overline{\text{PGOOD}}$ is an n-channel, open-drain, active-low output, referenced to V <sub>EE</sub> .
—	5	PGOOD	Power-Good Output. PGOOD is an n-channel, open-drain, active-high output, referenced to V <sub>EE</sub> .
6	6	ON/OFF	ON/OFF Control Input. ON/OFF is referenced to V <sub>EE</sub> . Drive ON/OFF above 1.38V or leave unconnected to enable the device. Drive ON/OFF below 1V to disable the device. ON/OFF is also used to adjust the UVLO threshold. See the <i>Under-voltage Lockout</i> section in the <i>Applications Information</i> . Internally clamped to nominally 3V through a 1k $\Omega$ resistor (see Figure 1).
—	—	EP	Exposed Pad (TDFN only). Connect to V <sub>EE</sub> .

## Detailed Description

The MAX5900/MAX5901 are integrated hot-swap controller ICs contained in 6-pin SOT23/TDFN packages. They allow a board to be safely hot plugged into a live backplane without causing a glitch on the power-supply rail. They are well suited for -48V telecom power systems, allowing a cost-effective, simple, and compact design. The MAX5900/MAX5901 operate from -9V to -100V to cover the standard telecom voltage range, and to serve more generalized applications. These devices require only an external n-channel power MOSFET to provide hot-swap control. Figure 1 shows a functional diagram of the MAX5900/MAX5901.

The MAX5900/MAX5901 control an external n-channel power MOSFET placed in the negative power-supply pathway. When power is first applied, the MAX5900/MAX5901 keep the MOSFET turned off. The MAX5900/MAX5901 hold the MOSFET off indefinitely if ON/OFF is held low, if the supply voltage is below the undervoltage lockout level, or if the die temperature exceeds +125°C. If none of these conditions exist for 300ms (typ), the MAX5900/MAX5901 begin to gradually turn on the MOSFET. During this turn-on phase, the MAX5900/MAX5901 slowly enhance the MOSFET,

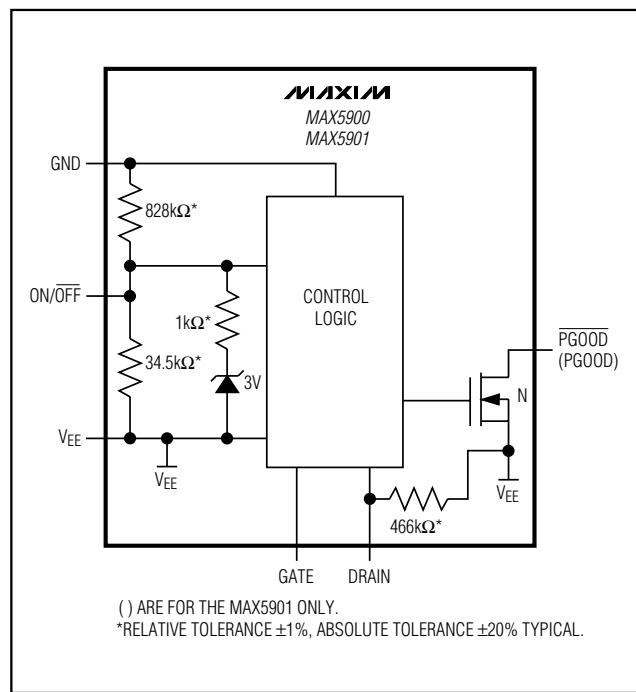


Figure 1. Functional Diagram

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allowing the voltage on the load, i.e. the drain of the MOSFET, to fall no faster than 10V/ms (typ). The inrush current to the load is thus limited to a level proportional to the load capacitance, and the constant load voltage slew rate. After the MOSFET is fully enhanced, and the load voltage is settled to its final value, the MAX5900A/MAX5901A and MAX5900L/MAX5901L monitor the voltage drop from the MOSFET's drain-to-source ( $V_{DS}$ ). If the voltage drop exceeds 75% of the circuit-breaker threshold the MAX5900A/MAX5901A or MAX5900L/MAX5901L turn off the MOSFET, disconnecting the load immediately. Because the circuit-breaker function is not activated until the MOSFET is fully enhanced, it takes approximately 10ms for the MAX5900A/MAX5901A or MAX5900L/MAX5901L to react to an output short circuit at startup. If no circuit-breaker fault exists, the power-good output is asserted. Then, if any of four conditions exist, the power-good output deasserts and the MOSFET is turned off. The four conditions are: the voltage across the MOSFET exceeds the circuit-breaker threshold; the supply voltage magnitude falls below the undervoltage lockout level; the die temperature exceeds +125°C; or ON/OFF is forced low. After a circuit-breaker fault, the MAX5900L/MAX5901L keep the MOSFET off until the power is cycled, or the part is reset by toggling ON/OFF low for at least 20ms (typ). After a circuit-breaker fault, the MAX5900A/MAX5901A automatically restart in 300ms (typ). All versions automatically restart after a thermal fault, or an undervoltage shutdown, if the fault condition goes away for at least 300ms (typ).

ON/OFF offers external control of the MAX5900/MAX5901, facilitating power-supply sequencing, and may also be used to change the UVLO level. UVLO keeps the external MOSFET switched off as long as the magnitude of the input voltage is less than a desired level.

A power-good output,  $\overline{\text{PGOOD}}$  (MAX5900) or PGOOD (MAX5901), asserts when the external MOSFET is fully enhanced and the drain-source voltage is at least 25% below the circuit-breaker threshold.  $\overline{\text{PGOOD}}$  and PGOOD are open-drain outputs referenced to  $V_{EE}$ , and can withstand up to 100V above  $V_{EE}$ .

A thermal shutdown feature protects the external MOSFET by turning it off if the die temperature of the MAX5900/MAX5901 exceeds +125°C. The MAX5900/MAX5901 must be in good thermal contact with the external MOSFET. See the *Layout Guidelines* section in the *Applications Information*.

A circuit-breaker function monitors the voltage across the external MOSFET,  $V_{DS}$ , and turns off the MOSFET if  $V_{DS}$  exceeds the circuit-breaker threshold,  $V_{CB}$ . The

circuit-breaker function is enabled after the MOSFET is fully enhanced. Three threshold voltage options are available—200mV, 300mV, and 400mV. One version is available with no circuit-breaker function. circuit-breaker fault management for the MAX5900/MAX5901 is offered with two different configurations—latched and automatic retry.

## Latched Circuit Breaker

After a circuit-breaker trip event, the latched versions (MAX5900L/MAX5901L) drive GATE to  $V_{EE}$ , turning off the external MOSFET, and  $\overline{\text{PGOOD}}$  (PGOOD) is deasserted. A latched-off condition needs to be reset by toggling ON/OFF low for at least 20ms, or by cycling the power supply,  $V_{EE}$ .

## Automatic Retry Circuit Breaker

After a circuit-breaker trip event, the automatic retry versions (MAX5900A/MAX5901A) drive GATE to  $V_{EE}$ , turning off the external MOSFET, and  $\overline{\text{PGOOD}}$  (PGOOD) is deasserted. If the start conditions are met for a full 300ms ( $t_{RS}$ ) the start sequence is initiated. The start conditions are: the device is not in UVLO; ON/OFF is not driven low; and the device is not in thermal shutdown.

## No Circuit Breaker

For the versions without a circuit-breaker MAX5900N (MAX5901N),  $\overline{\text{PGOOD}}$  (PGOOD) is asserted when the MOSFET is fully enhanced. Once powered up, the MAX5900N/MAX5901N ignore the MOSFET drain-to-source voltage ( $V_{DS}$ ) for applications where a circuit-breaker function is not desired.

## Applications Information

### ON/OFF Control Input

The ON/OFF control input provides three hot-swap functions: external ON/OFF control; setting of the UVLO level; and resetting after a circuit-breaker event has caused the MAX5900L/MAX5901L to turn off the external MOSFET. Pulling ON/OFF to  $V_{EE}$  for at least 20ms ( $t_{OFF}$ ) forces the MAX5900/MAX5901 to turn off the external MOSFET (see Figure 2 for a circuit example). To reset the MAX5900L/MAX5901L after a circuit-breaker event, toggle ON/OFF to  $V_{EE}$  for at least 20ms ( $t_{OFF}$ ).

ON/OFF can be used to sequence power supplies. Connecting a capacitor from ON/OFF to  $V_{EE}$  will delay the rise of ON/OFF proportional to the capacitance and input impedance of ON/OFF, typically 32k $\Omega$  (Figure 3).

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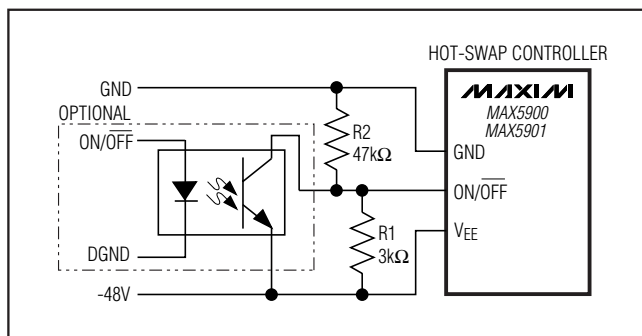


Figure 2. Programmed -20V Lockout With Optional Optocoupler On/Off Control

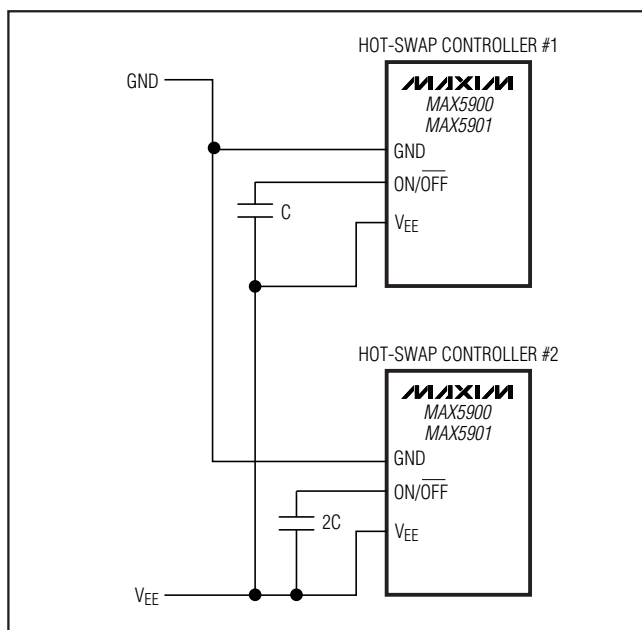


Figure 3. Power-Supply Sequencing

## Turn-On and Turn-Off Delays

After power is applied, or ON/OFF is released, there is a 300ms delay ( $t_{ON}$ ) before the gate ramp is started. This delay is also the automatic restart time delay.

In the event of a circuit-breaker condition or an over-temperature fault condition, the turn-off delay is less than 2μs. An undervoltage condition must exist for at least 20ms ( $t_{OFF}$ ) before the MAX5900/MAX5901 turn off the external MOSFET. ON/OFF must be held low for at least 20ms ( $t_{OFF}$ ) before the MAX5900/MAX5901 turn off the external MOSFET. Turn-off delay minimizes spurious shutdowns due to noisy signals or momentary

voltage spikes, as well as preventing accidental resetting of the circuit-breaker latch (MAX5900L/MAX5901L).

## Thermal Shutdown

A thermal shutdown feature helps protect the external MOSFET. If the die temperature of the MAX5900/MAX5901 exceeds +125°C, the MOSFET is turned off. For accurate performance, the MAX5900/MAX5901 must be in close thermal contact with the external MOSFET (see the *Layout Guidelines* section). Due to the low power dissipation of the MAX5900/MAX5901, its junction temperature will typically be within a few degrees of the MOSFET. All versions of the MAX5900/MAX5901 automatically restart from a temperature fault when the junction temperature drops below +110°C.

## Undervoltage Lockout

The MAX5900/MAX5901 turn off the external MOSFET if the magnitude of the input voltage is below the level set by ON/OFF for longer than 20ms ( $t_{OFF}$ ). If ON/OFF is left unconnected, the lockout voltage ( $V_{UVLO}$ ) defaults to -31.5V.  $V_{UVLO}$  may also be set to any value within the power-supply range by using external resistors. To set the lockout voltage to a value between -9V and -100V, use a resistor-divider connected between GND and VEE, with the center node of the divider connected to ON/OFF. For example, use a 3kΩ resistor (R1 in Figure 2) from ON/OFF to VEE and calculate the other resistor, R2, using:

$$R2 = R1 \times \left( \frac{V_{UVLO}}{1.26} - 1 \right)$$

where  $V_{UVLO}$  is the desired lockout voltage, and  $V_{ON/OFF}$  is the ON/OFF reference threshold specified in the *Electrical Characteristics* table (typically 1.26V).

Figure 2 shows an example circuit with  $V_{UVLO}$  set for -20V. To defeat the UVLO, simply connect a single 100kΩ resistor between ON/OFF and GND, as shown in Figure 4.

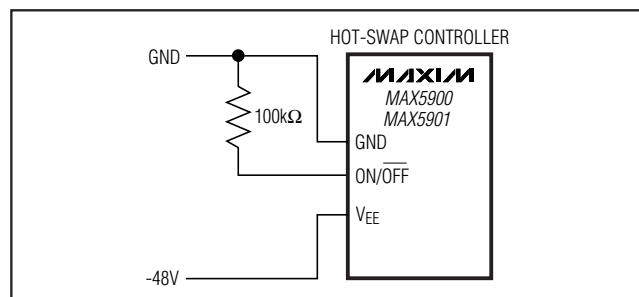


Figure 4. Defeating Undervoltage Lockout



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## Power-Good Output

The power-good output,  $\overline{\text{PGOOD}}$  (PGOOD), is open-drain and asserts when the external MOSFET is fully enhanced and  $V_{DS}$  is less than  $V_{PG}$  (75% of the circuit-breaker threshold,  $V_{CB}$ ). For versions without the circuit-breaker function (MAX5900N/MAX5901N),  $\overline{\text{PGOOD}}$  (PGOOD) asserts when the external MOSFET is fully enhanced.

$\overline{\text{PGOOD}}$  (PGOOD) deasserts within 2 $\mu$ s when a circuit-breaker event occurs or if the die temperature exceeds +125°C.  $\overline{\text{PGOOD}}$  (PGOOD) deasserts if  $|V_{EE}| < |V_{UVLO}|$  for longer than 20ms or ON/OFF is held low for longer than 20ms.

The MAX5900  $\overline{\text{PGOOD}}$  is active-low and the MAX5901 PGOOD is active-high. Both are open-drain N-channel MOSFETs with their sources connected to  $V_{EE}$ , and can withstand up to 100V.

## Selecting a Circuit-Breaker Threshold

The MAX5900A/MAX5901A and the MAX5900L/MAX5901L offer a circuit-breaker function to protect the external MOSFET and the load from the potentially damaging effects of excessive current. As load current flows through the external MOSFET, a voltage,  $V_{DS}$ , is generated from drain to source due to the MOSFET's on-resistance  $R_{DS(ON)}$ . The MAX5900A/MAX5901A and MAX5900L/MAX5901L monitor  $V_{DS}$  when the external MOSFET is fully enhanced. If  $V_{DS}$  exceeds the circuit-breaker threshold, the external MOSFET is turned off and  $\overline{\text{PGOOD}}$  (PGOOD) is deasserted.

To accommodate different MOSFETs and different load currents, the MAX5900/MAX5901 are available with circuit-breaker threshold voltages of 200mV, 300mV, and 400mV.

The circuit-breaker function is intended to disconnect the load if a gross overcurrent or short-circuit condition occurs. For calculating the circuit-breaker threshold, use the MOSFET's  $R_{ON}$  at the worst possible operating condition, and add a 25% overcurrent margin to the maximum circuit current. For instance, if a MOSFET has an  $R_{ON}$  of 0.06 $\Omega$  at  $T_A = +25^\circ\text{C}$ , and a normalized on-resistance factor of 1.75 at  $T_A = +130^\circ\text{C}$  (from the MOSFET data sheet), the  $R_{ON}$  used for calculation is the product of these two numbers, or (0.06 $\Omega$ )  $\times$  (1.75) = 0.105 $\Omega$ . Then, if the maximum current is expected to be 2A, using a 25% margin, the current for calculation is (2A)  $\times$  (1.25) = 2.5A. The resulting minimum circuit-breaker threshold is then the product of these two results, or (0.105 $\Omega$ )  $\times$  (2.5A) = 0.263V. The next highest minimum available threshold is 0.265V of the MAX590\_ \_BEUT, which is an ideal choice given these parameters. Using this method to choose a circuit-

breaker threshold allows the circuit to operate under worst-case conditions without causing a circuit-breaker fault, but the circuit-breaker function will still operate if a short-circuit or gross overcurrent condition occurs. See Table 1 for MOSFET suggestions. The MAX5900N/MAX5901N have no circuit-breaker function. For these parts choose an external MOSFET that meets the load requirements.

## Determining Inrush Current

Determining a circuit's inrush current is necessary to help choose the proper MOSFET. The MAX5900/MAX5901 regulate the inrush current by means of controlling the load voltage slew rate, but inrush current is also a function of load capacitance. Determine inrush current using:

$$I = C \frac{dV}{dt} = C \times SR$$

where C is the load capacitance, and SR is the MAX5900/MAX5901 Load Voltage Slew-Rate Magnitude from the *Electrical Characteristics* table. For example, assuming a load capacitance of 100 $\mu$ F, and using the typical value of 10V/ms for the slew rate, the inrush current is 1A typical.

If the maximum possible Load Voltage Slew Rate is used, the maximum inrush current calculates to 1.7A. Choose a MOSFET with a maximum pulsed current specification that exceeds the maximum inrush current.

## Suggested External MOSFETs

MAXIMUM LOAD (A)	SUGGESTED EXTERNAL MOSFET	SUGGESTED MAXIM PART
0.25	IRFL110	MAX590_ _CEUT
0.5	IRFL4310	MAX590_ _BEUT
1	IRFR3910	MAX590_ _CEUT
2	IRF540NS	MAX590_ _BEUT
3	IRF1310NS	MAX590_ _BEUT
4	IRF1310NS	MAX590_ _CEUT

$V_{IN} = -9V$  to  $-90V$

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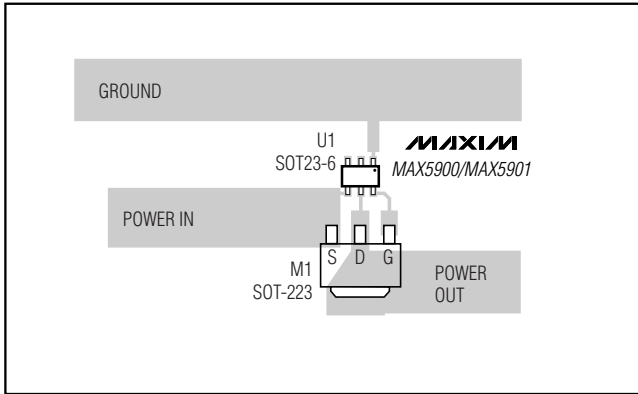


Figure 5. Circuit Board Layout Example

## Layout Guidelines

Good thermal contact between the MAX5900/MAX5901 and the external MOSFET is essential for the thermal shutdown feature to operate effectively. Place the MAX5900/MAX5901 as close as possible to the drain of the external MOSFET, and use wide circuit board traces for good heat transfer. See Figure 5 for an example of a PC board layout.

## Chip Information

TRANSISTOR COUNT: 678

PROCESS: BiCMOS

MAX5900/MAX5901

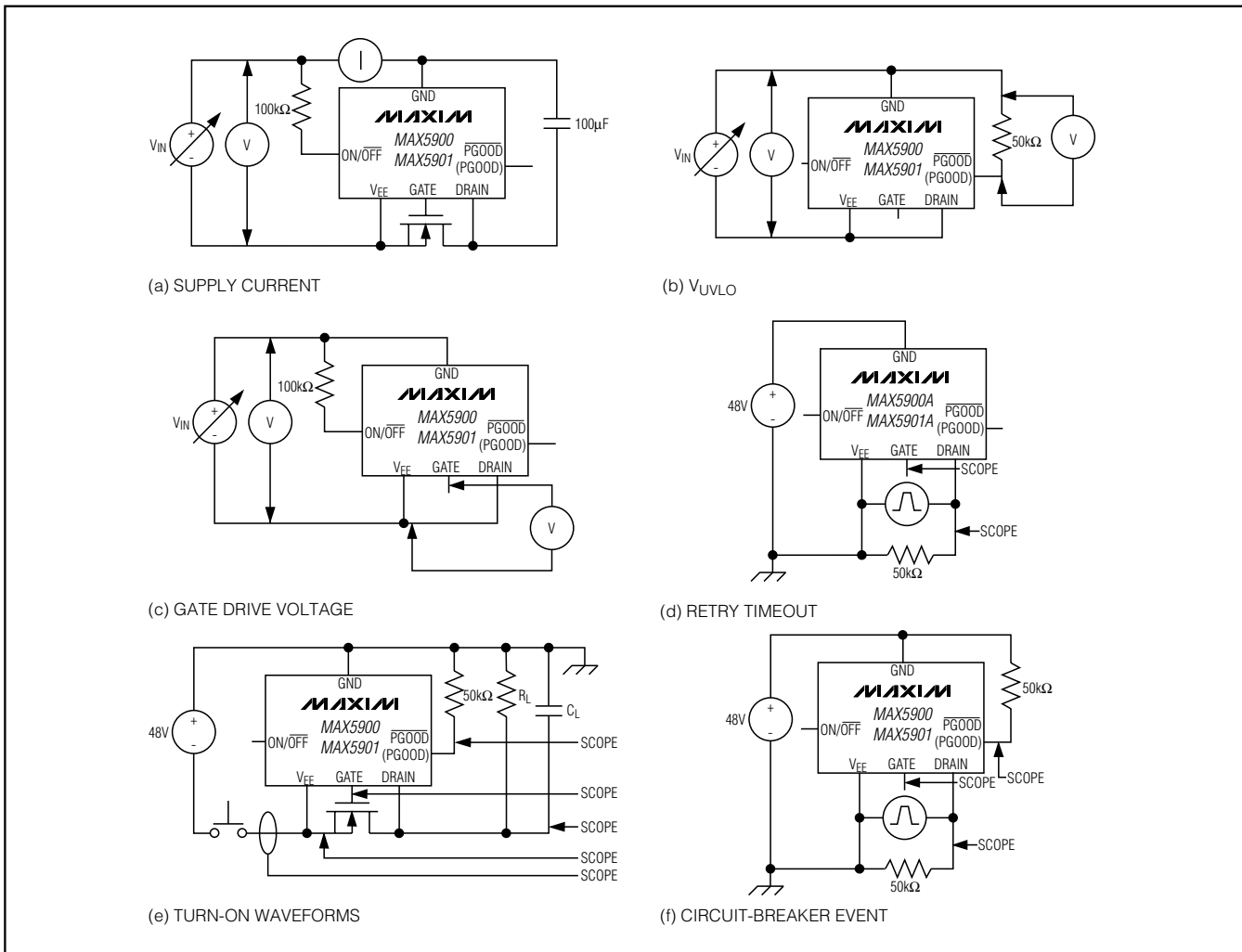


Figure 6. Test Circuits



# -100V, SOT23/TDFN, Simple Swapper Hot-Swap Controllers

## Selector Guide

### SOT23

PART	CIRCUIT-BREAKER FUNCTION	CIRCUIT-BREAKER THRESHOLD (mV)	POWER-GOOD OUTPUT LOGIC	TOP MARK
MAX5900NNEUT+T	None	None	Active-Low	AAQV
MAX5900AAEUT+T	Autoretry	200	Active-Low	AAQJ
MAX5900ABEUT+T	Autoretry	300	Active-Low	AAQK
MAX5900ACEUT+T	Autoretry	400	Active-Low	AAQL
MAX5900LAEUT+T	Latched	200	Active-Low	AAQM
MAX5900LBEUT+T	Latched	300	Active-Low	AAQN
MAX5900LCEUT+T	Latched	400	Active-Low	AAQO
MAX5901NNEUT+T	None	None	Active-High	AAQW
MAX5901AAEUT+T	Autoretry	200	Active-High	AAQP
MAX5901ABEUT+T	Autoretry	300	Active-High	AAQQ
MAX5901ACEUT+T	Autoretry	400	Active-High	AAQR
MAX5901LAEUT+T	Latched	200	Active-High	AAQS
MAX5901LBEUT+T	Latched	300	Active-High	AAQT
MAX5901LCEUT+T	Latched	400	Active-High	AAQU

### TDFN

PART	CIRCUIT-BREAKER FUNCTION	CIRCUIT-BREAKER THRESHOLD (mV)	POWER-GOOD OUTPUT LOGIC	TOP MARK
MAX5900NNETT+T	None	None	Active-Low	AJT
MAX5900AAETT+T	Autoretry	200	Active-Low	AJU
MAX5900ABETT+T	Autoretry	300	Active-Low	AJV
MAX5900ACETT+T	Autoretry	400	Active-Low	AJW
MAX5900LAETT+T	Latched	200	Active-Low	AJX
MAX5900LBETT+T	Latched	300	Active-Low	AJY
MAX5900LCETT+T	Latched	400	Active-Low	AJZ
MAX5901NNETT+T	None	None	Active-High	AKA
MAX5901AAETT+T	Autoretry	200	Active-High	AKB
MAX5901ABETT+T	Autoretry	300	Active-High	AKC
MAX5901ACETT+T	Autoretry	400	Active-High	AKD
MAX5901LAETT+T	Latched	200	Active-High	AKE
MAX5901LBETT+T	Latched	300	Active-High	AKF
MAX5901LCETT+T	Latched	400	Active-High	AKG

+Denotes lead-free package.

# MAX5900/MAX5901

[illegible]

TOP VIEW

Pin configuration diagram for the MAX5900 in a 3mm x 3mm TDFN package. The diagram shows a square package with pins 1 through 6. Pin 1 is VEE, Pin 2 is DRAIN, Pin 3 is GATE, Pin 4 is GND, Pin 5 is PG00D (PG00D), and Pin 6 is ON/OFF. The package is labeled MAX5900 and MAX5901. A note indicates that the exposed pad is connected to VEE.

MAX5900  
MAX5901

\* EXPOSED PAD

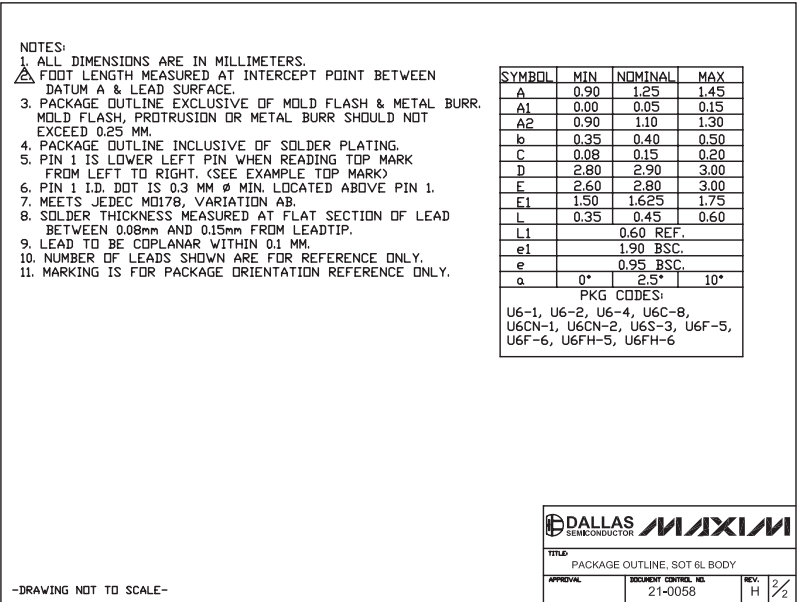
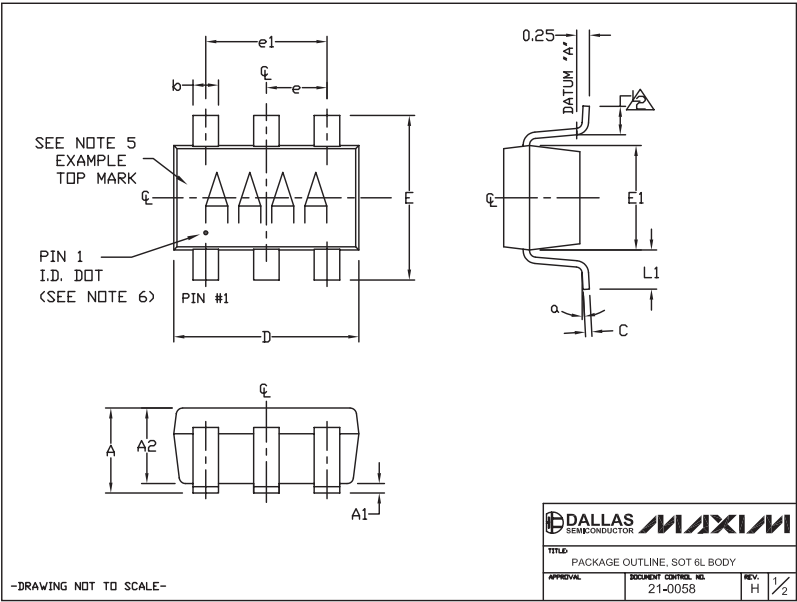
**TDFN**  
**3mm x 3mm**

( ) ARE FOR MAX5901 ONLY.  
\* EXPOSED PAD CONNECTED TO V<sub>EE</sub>.

# -100V, SOT23/TDFN, Simple Swapper Hot-Swap Controllers

## Package Information

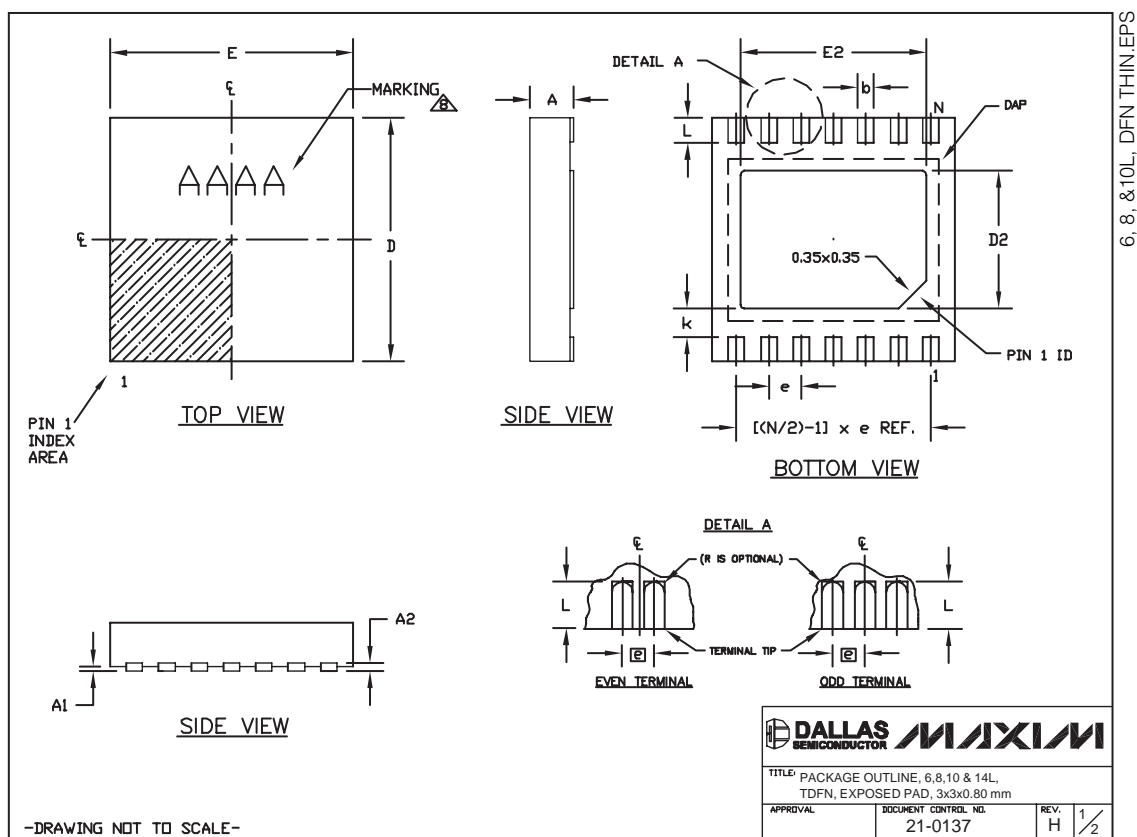
(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to [www.maxim-ic.com/packages](http://www.maxim-ic.com/packages).)



# -100V, SOT23/TDFN, Simple Swapper Hot-Swap Controllers

## Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to [www.maxim-ic.com/packages](http://www.maxim-ic.com/packages).)



MAX5900/MAX5901

# -100V, SOT23/TDFN, Simple Swapper Hot-Swap Controllers

## Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to [www.maxim-ic.com/packages](http://www.maxim-ic.com/packages).)

COMMON DIMENSIONS		
SYMBOL	MIN.	MAX.
A	0.70	0.80
D	2.90	3.10
E	2.90	3.10
A1	0.00	0.05
L	0.20	0.40
k	0.25 MIN.	
A2	0.20 REF.	

PACKAGE VARIATIONS								
PKG. CODE	N	D2	E2	e	JEDEC SPEC	b	[(N/2)-1] x e	
T633-1	6	1.50±0.10	2.30±0.10	0.95 BSC	MO229 / WEEA	0.40±0.05	1.90 REF	
T633-2	6	1.50±0.10	2.30±0.10	0.95 BSC	MO229 / WEEA	0.40±0.05	1.90 REF	
T833-1	8	1.50±0.10	2.30±0.10	0.65 BSC	MO229 / WEEC	0.30±0.05	1.95 REF	
T833-2	8	1.50±0.10	2.30±0.10	0.65 BSC	MO229 / WEEC	0.30±0.05	1.95 REF	
T833-3	8	1.50±0.10	2.30±0.10	0.65 BSC	MO229 / WEEC	0.30±0.05	1.95 REF	
T1033-1	10	1.50±0.10	2.30±0.10	0.50 BSC	MO229 / WEED-3	0.25±0.05	2.00 REF	
T1033-2	10	1.50±0.10	2.30±0.10	0.50 BSC	MO229 / WEED-3	0.25±0.05	2.00 REF	
T1433-1	14	1.70±0.10	2.30±0.10	0.40 BSC	----	0.20±0.05	2.40 REF	
T1433-2	14	1.70±0.10	2.30±0.10	0.40 BSC	----	0.20±0.05	2.40 REF	

### NOTES:

1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
2. COPLANARITY SHALL NOT EXCEED 0.08 mm.
3. WARPAGE SHALL NOT EXCEED 0.10 mm.
4. PACKAGE LENGTH/PACKAGE WIDTH ARE CONSIDERED AS SPECIAL CHARACTERISTIC(S).
5. DRAWING CONFORMS TO JEDEC MO229, EXCEPT DIMENSIONS "D2" AND "E2", AND T1433-1 & T1433-2.
6. "N" IS THE TOTAL NUMBER OF LEADS.
7. NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.

▲ MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY.

-DRAWING NOT TO SCALE-

			
<b>TITLE:</b> PACKAGE OUTLINE, 6,8,10 & 14L, TDFN, EXPOSED PAD, 3x3x0.80 mm			
<b>APPROVAL</b>	<b>DOCUMENT CONTROL NO.</b>	<b>REV.</b>	
	21-0137	H	2/2

## Revision History

Pages changed at Rev 5: 1-4, 10, 12-14

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

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